Electronic Supporting Information

Tailoring Ga_2O_3 Epitaxial Films on Sapphire: Impact of Gallium Ligand Precursors and Growth Temperature Using Mist-CVD

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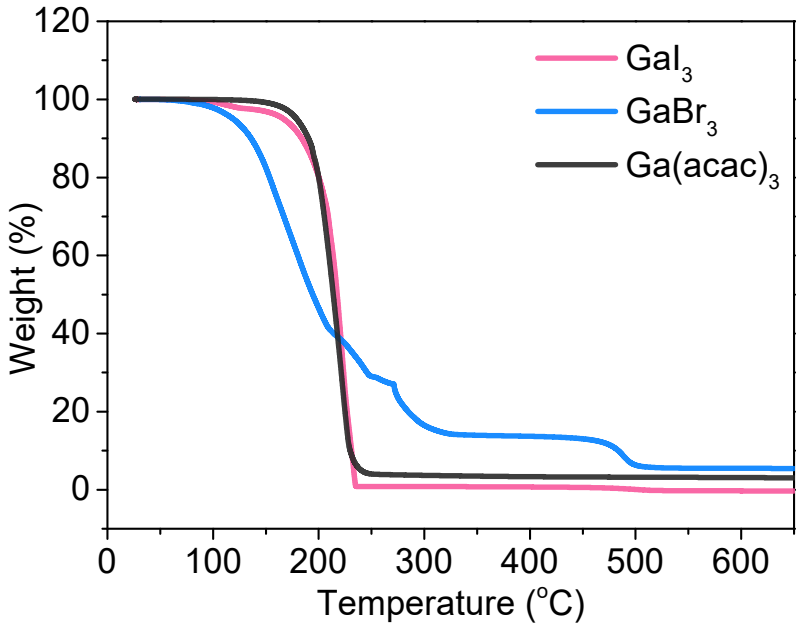

Fig. S1 TGA (thermogravimetric analysis) curves of $Ga(acac)_3$, GaI_3 and $GaBr_3$ precursors.

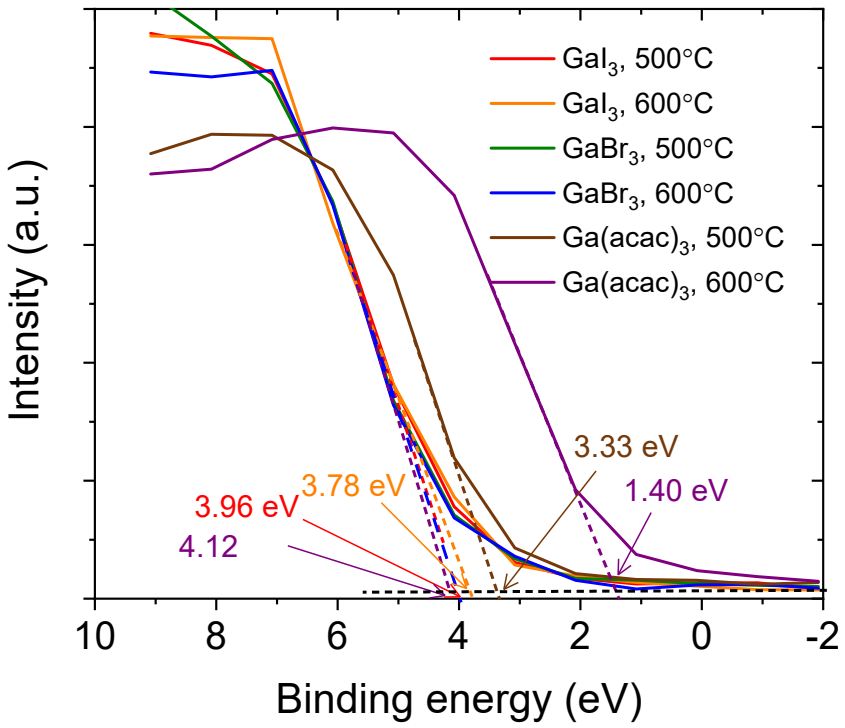

Fig. S2 UPS spectra of the valance band maximum of ε-Ga_2O_3 epitaxial films with different gallium precursors and growth temperatures.

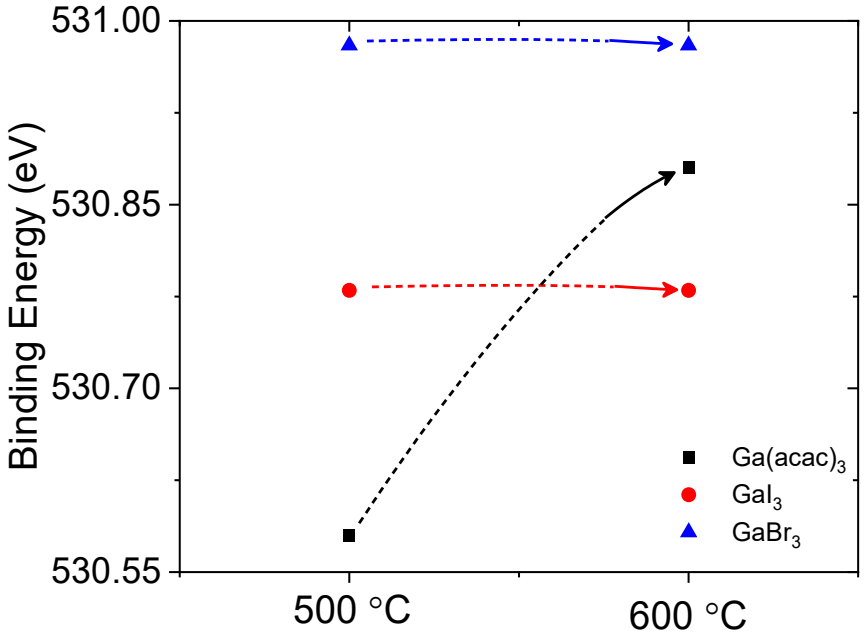

Fig. S3 Comparison of binding energy of ε-Ga_2O_3 epitaxial films from O1s level with different gallium precursors and growth temperatures from 500 ºC and 600 ºC.